

n-channel JFET designed for . . .



Performance Curves NH/NRL See Section 4

- VHF/UHF Amplifiers
- Mixers
- Oscillators

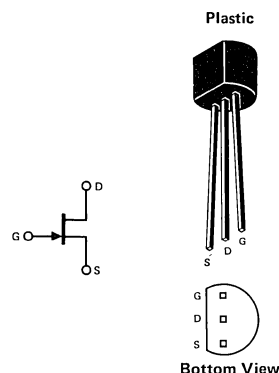
BENEFITS

- Low Cost
- Automatic Insertion Package

ABSOLUTE MAXIMUM RATINGS (25°C)

Drain-Gate Voltage	25 V
Source-Gate Voltage	25 V
Drain-Source Voltage	25 V
Forward Gate Current	10 mA
Total Device Dissipation at 25°C Ambient (Derate 3.27 mW/°C)	360 mW
Operating Temperature Range	–55 to 135°C
Storage Temperature Range	–55 to 150°C
Lead Temperature Range (1/16" from case for 10 seconds)	300°C

TO-92
See Section 6



ELECTRICAL CHARACTERISTICS (25°C unless otherwise noted)

Characteristic			Min	Max	Unit	Test Conditions		
1	S T A T I C	IGSS	Gate Reverse Current		−2.0	nA	VGS = −15 V, VDS = 0	TA = +100°C
2					−2.0	μA		
3		BVGSS	Gate-Source Breakdown Voltage	−25		V	IG = −10 μA, VDS = 0	
4		VGS(off)	Gate-Source Cutoff Voltage		−8.0		VDS = 15 V, ID = 2 nA	
5		IDSS	Saturation Drain Current	2.0	20	mA	VDS = 15 V, VGS = 0 (Note 1)	
6		VGS	Gate-Source Voltage	−0.5	−7.5	V	VDS = 15 V, ID = 200 μA	
7	D Y N A M I C	gfs	Common-Source Forward Transconductance	2000	7500	μmhos	VDS = 15 V, VGS = 0	f = 1 kHz
8		Re(yfs)	Common-Source Forward Transconductance	1600				f = 100 MHz
9		Re(yos)	Common-Source Output Conductance		200			
10		Re(yis)	Common-Source Input Conductance		800			f = 1 MHz
11		Ciss	Common-Source Input Capacitance		7.0	pF		
12		Crss	Common-Source Reverse Transfer Capacitance		3.0			

NOTE:

1. Pulse test $PW = 300\text{ }\mu\text{s}$; duty cycle $\leq 3\%$.

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